



CYPRESS

PRELIMINARY

CY7C1049

512K x 8 Static RAM

Features

- **High speed**
 - $t_{AA} = 15 \text{ ns}$
- **Low active power**
 - 1210 mW (max.)
- **Low CMOS standby power (Commercial L version)**
 - 2.75 mW (max.)
- **2.0V Data Retention (400 μW at 2.0V retention)**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with $\overline{\text{CE}}$ and $\overline{\text{OE}}$ features**

Functional Description

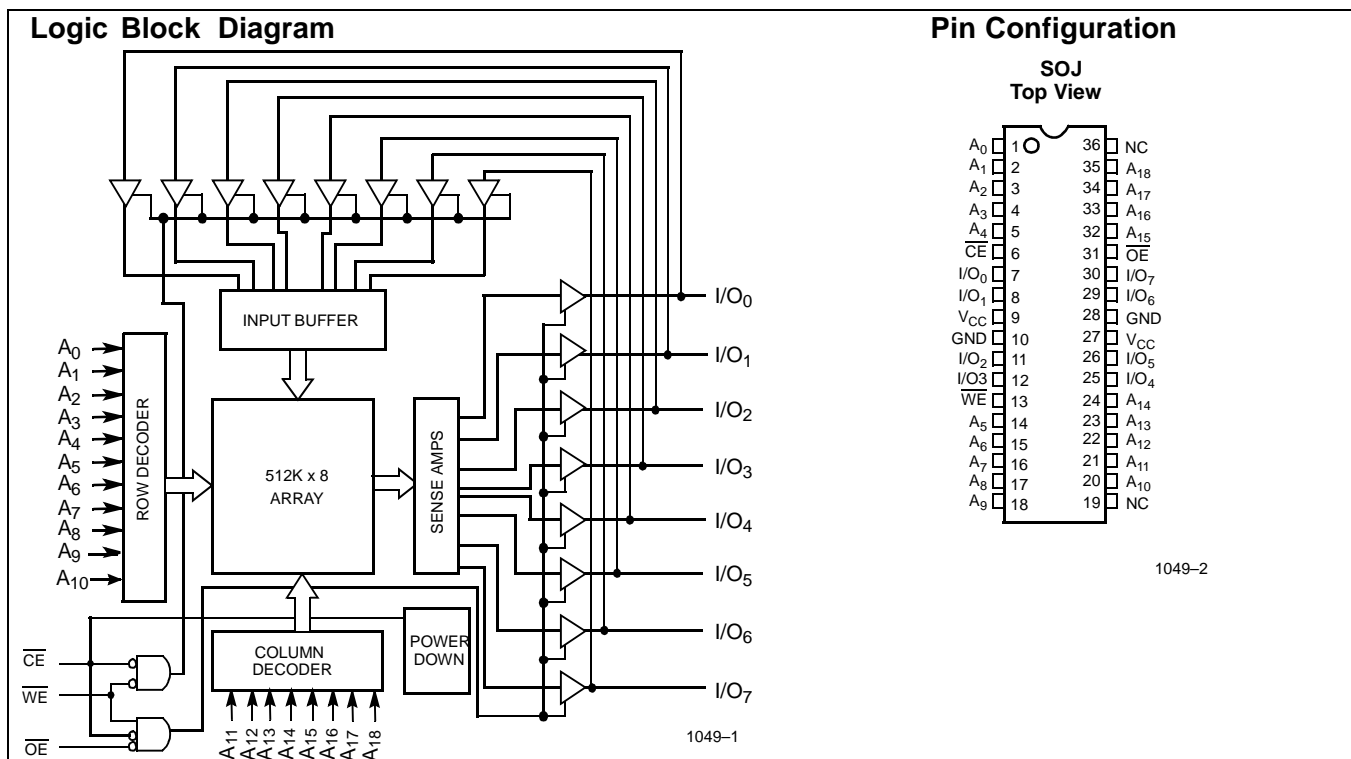
The CY7C1049 is a high-performance CMOS static RAM organized as 524,288 words by 8 bits. Easy memory expansion

is provided by an active LOW chip enable ($\overline{\text{CE}}$), an active LOW output enable ($\overline{\text{OE}}$), and three-state drivers. Writing to the device is accomplished by taking chip enable ($\overline{\text{CE}}$) and write enable ($\overline{\text{WE}}$) inputs LOW. Data on the eight I/O pins (I/O₀ through I/O₇) is then written into the location specified on the address pins (A₀ through A₁₈).

Reading from the device is accomplished by taking chip enable ($\overline{\text{CE}}$) and output enable ($\overline{\text{OE}}$) LOW while forcing write enable ($\overline{\text{WE}}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O₀ through I/O₇) are placed in a high-impedance state when the device is deselected ($\overline{\text{CE}}$ HIGH), the outputs are disabled ($\overline{\text{OE}}$ HIGH), or during a write operation ($\overline{\text{CE}}$ LOW, and $\overline{\text{WE}}$ LOW).

The CY7C1049 is available in a standard 400-mil-wide 36-pin SOJ package with center power and ground (revolutionary) pinout.



Selection Guide

		7C1049-12	7C1049-15	7C1049-17	7C1049-20	7C1049-25
Maximum Access Time (ns)		12	15	17	20	25
Maximum Operating Current (mA)		240	220	195	185	180
Maximum CMOS Standby Current (mA)	Com'l	8	8	8	8	8
	Com'l L	0.5	0.5	0.5	0.5	0.5
	Ind'l	9	9	9	9	9
	Military				10	10

Shaded areas contain advance information.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with

Power Applied..... -55°C to +125°C

Supply Voltage on V_{CC} to Relative GND^[1] -0.5V to +7.0V

DC Voltage Applied to Outputs

in High Z State^[1] -0.5V to $V_{CC} + 0.5V$

DC Input Voltage^[1] -0.5V to $V_{CC} + 0.5V$

Current into Outputs (LOW) 20 mA

Static Discharge Voltage >2001V
(per MIL-STD-883, Method 3015)

Latch-Up Current..... >200 mA

Operating Range

Range	Ambient Temperature ^[2]	V_{CC}
Commercial	0°C to +70°C	4.5V–5.5V
Industrial	-40°C to +85°C	
Military	-55°C to +125°C	

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	7C1049-12		7C1049-15		7C1049-17		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}, I_{OH} = -4.0 \text{ mA}$	2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min.}, I_{OL} = 8.0 \text{ mA}$		0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.2	$V_{CC} + 0.3$	2.2	$V_{CC} + 0.3$	2.2	$V_{CC} + 0.3$	V
V_{IL}	Input LOW Voltage ^[1]		-0.3	0.8	-0.3	0.8	-0.3	0.3	V
I_{IX}	Input Load Current	$GND \leq V_I \leq V_{CC}$	-1	+1	-1	+1	-1	+1	μA
I_{OZ}	Output Leakage Current	$GND \leq V_{OUT} \leq V_{CC}$, Output Disabled	-1	+1	-1	+1	-1	+1	μA
I_{CC}	V_{CC} Operating Supply Current	$V_{CC} = \text{Max.}$ $f = f_{MAX} = 1/t_{RC}$		240		220		195	mA
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC} , $\overline{CE} \geq V_{IH}$ $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$, $f = f_{MAX}$		40		40		40	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC} , $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$, or $V_{IN} \leq 0.3V$, $f=0$	Com'l			8		8	mA
			Com'l L			0.5		0.5	mA
			Ind'l			9		9	mA
			Military			10		10	mA

Shaded areas contain advance information.

Notes:

- V_{IL} (min.) = -2.0V for pulse durations of less than 20 ns.
- T_A is the "instant on" case temperature.

Electrical Characteristics Over the Operating Range (continued)

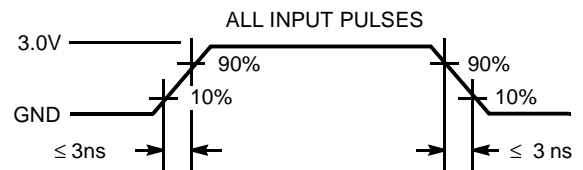
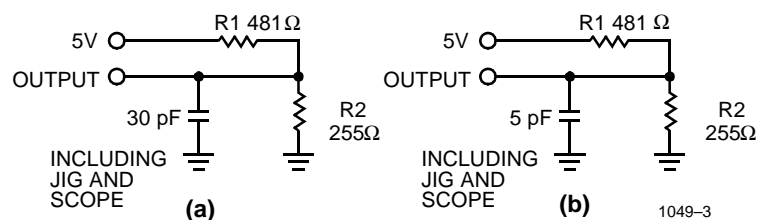
Parameter	Description	Test Conditions		7C1049-20		7C1049-25		Unit	
				Min.	Max.	Min.	Max.		
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = −4.0 mA		2.4		2.4		V	
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA			0.4		0.4	V	
V _{IH}	Input HIGH Voltage			2.2	V _{CC} + 0.3	2.2	V _{CC} + 0.3	V	
V _{IL}	Input LOW Voltage ^[1]			−0.3	0.8	−0.3	0.8	V	
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}		−1	+1	−1	+1	μA	
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , Output Disabled		−1	+1	−1	+1	μA	
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., f = f _{MAX} = 1/t _{RC}			185		180	mA	
I _{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V _{CC} , CE ≥ V _{IH} V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}			40		40	mA	
I _{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} − 0.3V, V _{IN} ≥ V _{CC} − 0.3V, or V _{IN} ≤ 0.3V, f=0	Com'I		8		8	mA	
			Com'I	L		0.5		0.5	mA
			Ind'I			9		9	mA
			Military			10		10	mA

Capacitance^[3]

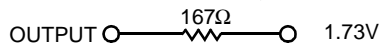
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$, $V_{CC} = 5.0\text{V}$	8	pF
C_{OUT}	I/O Capacitance		8	pF

Note:

3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms


Equivalent to: THÉVENIN EQUIVALENT



Switching Characteristics^[4] Over the Operating Range

Parameter	Description	7C1049-12		7C1049-15		7C1049-17		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE								
t _{RC}	Read Cycle Time	12		15		17		ns
t _{AA}	Address to Data Valid		12		15		17	ns
t _{OHA}	Data Hold from Address Change	3		3		3		ns
t _{ACE}	\overline{CE} LOW to Data Valid		12		15		17	ns
t _{DOE}	\overline{OE} LOW to Data Valid		6		7		8	ns
t _{LZOE}	\overline{OE} LOW to Low Z ^[6]	0		0		0		ns
t _{HZOE}	\overline{OE} HIGH to High Z ^[5, 6]		6		7		7	ns
t _{LZCE}	\overline{CE} LOW to Low Z ^[6]	3		3		3		ns
t _{HZCE}	\overline{CE} HIGH to High Z ^[5, 6]		6		7		7	ns
t _{PU}	\overline{CE} LOW to Power-Up	0		0		0		ns
t _{PD}	\overline{CE} HIGH to Power-Down		12		15		17	ns
WRITE CYCLE ^[7,8]								
t _{WC}	Write Cycle Time	12		15		17		ns
t _{SCE}	\overline{CE} LOW to Write End	10		12		12		ns
t _{AW}	Address Set-Up to Write End	10		12		12		ns
t _{HA}	Address Hold from Write End	0		0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		ns
t _{PWE}	\overline{WE} Pulse Width	10		12		12		ns
t _{SD}	Data Set-Up to Write End	7		8		8		ns
t _{HD}	Data Hold from Write End	0		0		0		ns
t _{LZWE}	\overline{WE} HIGH to Low Z ^[6]	3		3		3		ns
t _{HZWE}	\overline{WE} LOW to High Z ^[5, 6]		6		7		8	ns

Shaded areas contain advance information.

Notes:

- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- The internal write time of the memory is defined by the overlap of \overline{CE} LOW, and \overline{WE} LOW. \overline{CE} and \overline{WE} must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle no. 3 (\overline{WE} controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD} .

Switching Characteristics^[4] Over the Operating Range (continued)

Parameter	Description	7C1049-20		7C1049-25		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t _{RC}	Read Cycle Time	20		25		ns
t _{AA}	Address to Data Valid		20		25	ns
t _{OHA}	Data Hold from Address Change	3		5		ns
t _{ACE}	\overline{CE} LOW to Data Valid		20		25	ns
t _{DOE}	\overline{OE} LOW to Data Valid		8		10	ns
t _{LZOE}	\overline{OE} LOW to Low Z ^[6]	0		0		ns
t _{HZOE}	\overline{OE} HIGH to High Z ^[5, 6]		8		10	ns
t _{LZCE}	\overline{CE} LOW to Low Z ^[6]	3		5		ns
t _{HZCE}	\overline{CE} HIGH to High Z ^[5, 6]		8		10	ns
t _{PU}	\overline{CE} LOW to Power-Up	0		0		ns
t _{PD}	\overline{CE} HIGH to Power-Down		20		25	ns
WRITE CYCLE ^[7]						
t _{WC}	Write Cycle Time	20		25		ns
t _{SCE}	\overline{CE} LOW to Write End	13		15		ns
t _{AW}	Address Set-Up to Write End	13		15		ns
t _{HA}	Address Hold from Write End	0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		ns
t _{PWE}	\overline{WE} Pulse Width	13		15		ns
t _{SD}	Data Set-Up to Write End	9		10		ns
t _{HD}	Data Hold from Write End	0		0		ns
t _{LZWE}	\overline{WE} HIGH to Low Z ^[6]	3		5		ns
t _{HZWE}	\overline{WE} LOW to High Z ^[5, 6]		8		10	ns

Data Retention Characteristics Over the Operating Range

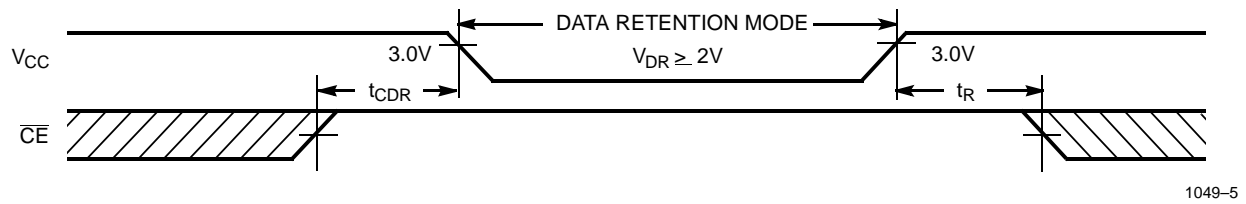
Parameter	Description			Conditions ^[10]	Min.	Max	Unit
V _{DR}	V _{CC} for Data Retention				2.0		V
I _{CCDR}	Data Retention Current	Com'l	L	V _{CC} = V _{DR} = 3.0V, CE ≥ V _{CC} − 0.3V V _{IN} ≥ V _{CC} − 0.3V or V _{IN} ≤ 0.3V		200	μA
		Ind'l				1	mA
		Military				2	mA
t _{CDR} ^[3]	Chip Deselect to Data Retention Time				0		ns
t _R ^[9]	Operation Recovery Time				t _{RC}		ns

Notes:

9. $t_r \leq 3$ ns for the -12 and -15 speeds. $t_r \leq 5$ ns for the -20 ns and slower speeds.

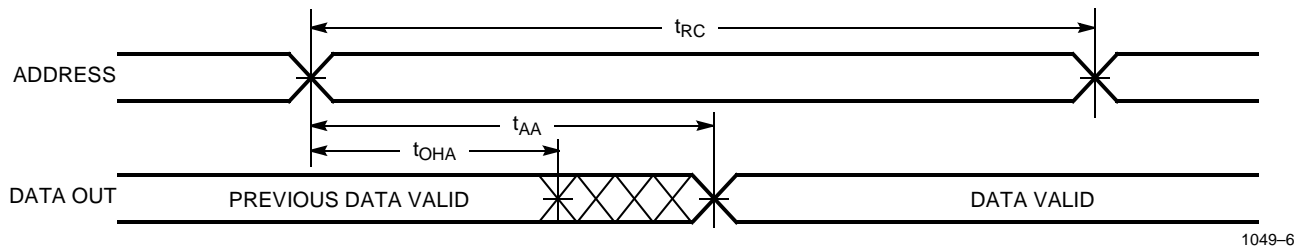
10. No input may exceed $V_{CC} + 0.5V$.

Data Retention Waveform

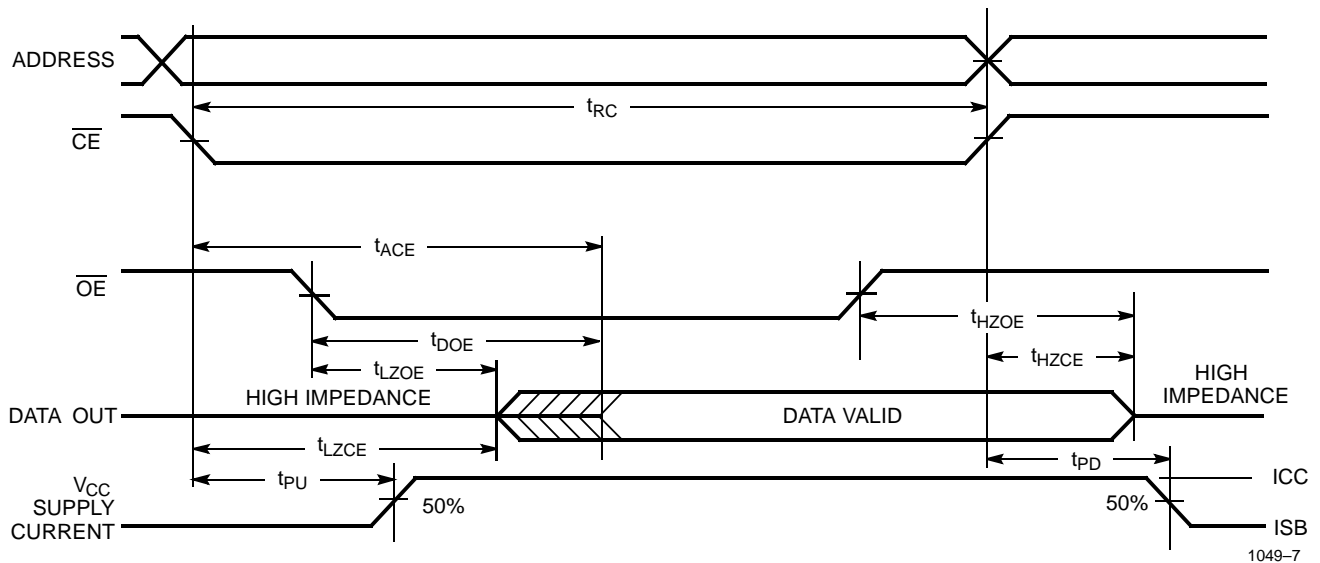


Switching Waveforms

Read Cycle No. 1^[11, 12]

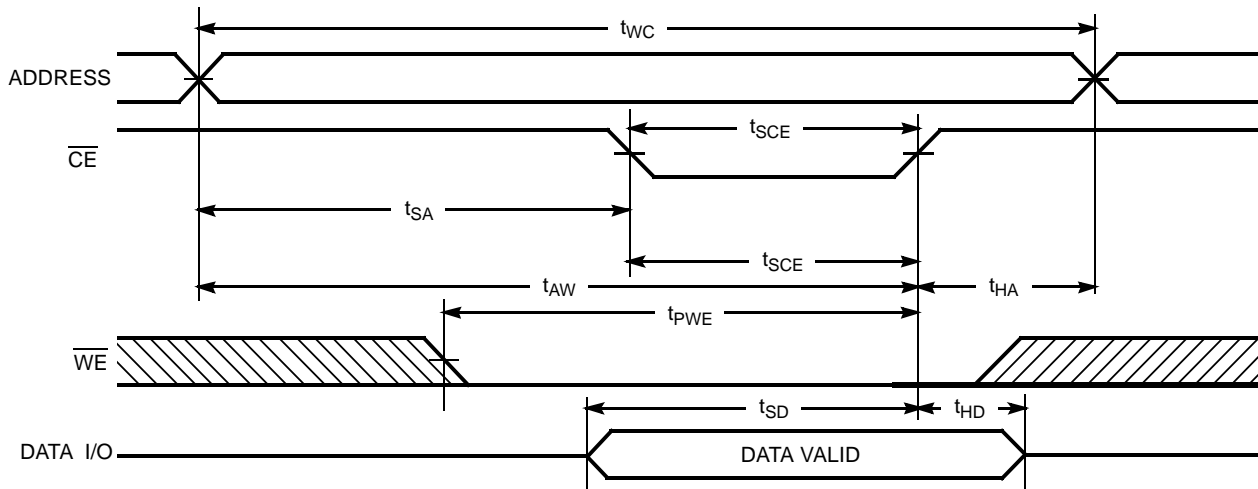


Read Cycle No. 2 (OE Controlled)^[12, 13]

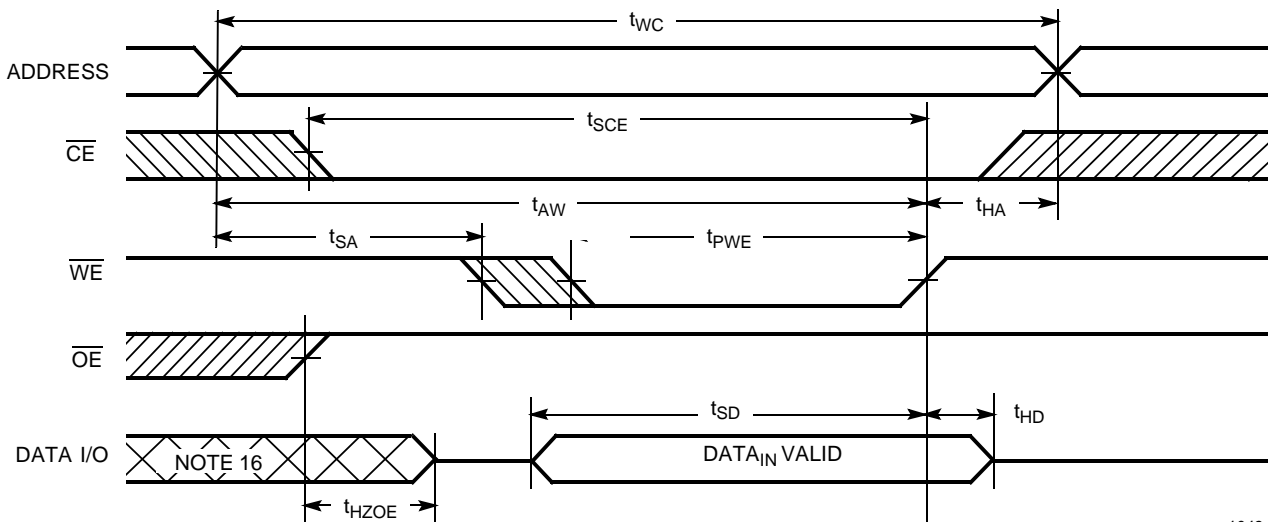


Notes:

11. Device is continuously selected. $\overline{OE}, \overline{CE} = V_{IL}$.
12. \overline{WE} is HIGH for read cycle.
13. Address valid prior to or coincident with \overline{CE} transition LOW.

Switching Waveforms (continued)
Write Cycle No. 1 ($\overline{\text{CE}}$ Controlled)^[14, 15]


1049-8

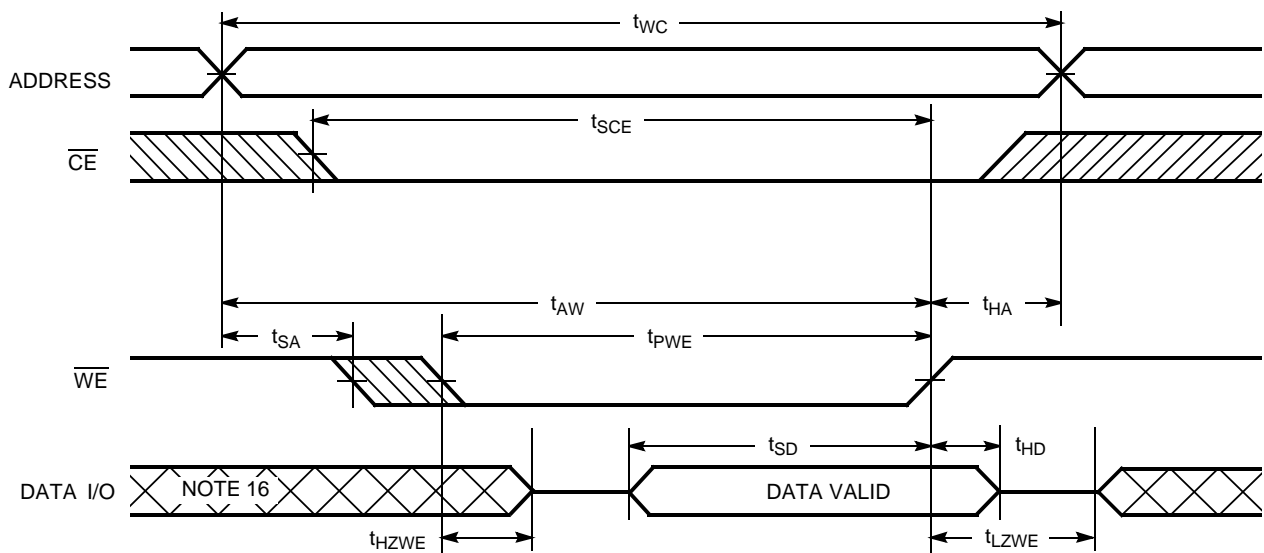
Write Cycle No. 2 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ HIGH During Write)^[14, 15]


1049-9

Notes:

14. Data I/O is high impedance if $\overline{\text{OE}} = V_{IH}$.
15. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ going HIGH, the output remains in a high-impedance state.
16. During this period the I/Os are in the output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[15]


1049-10

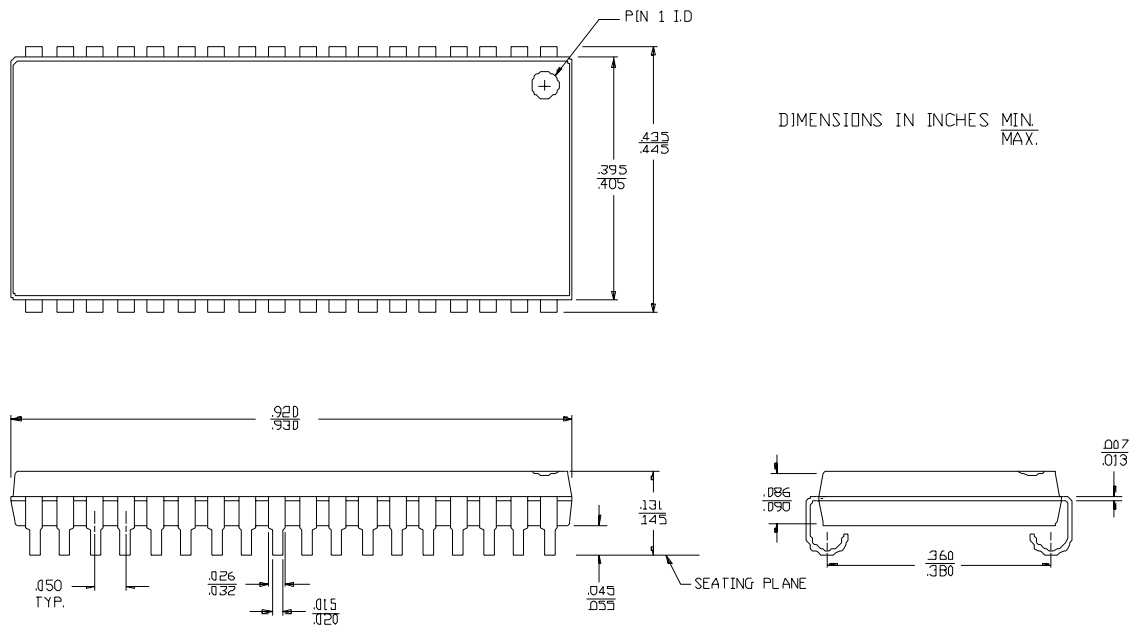
Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C1049-15VC	V36	36-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1049L-15VC	V36	36-Lead (400-Mil) Molded SOJ	
17	CY7C1049-17VC	V36	36-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1049L-17VC	V36	36-Lead (400-Mil) Molded SOJ	
20	CY7C1049-20VC	V36	36-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1049L-20VC	V36	36-Lead (400-Mil) Molded SOJ	
	CY7C1049-20VI	V36	36-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1049L-20VI	V36	36-Lead (400-Mil) Molded SOJ	
	CY7C1049-20VM	V36	36-Lead (400-Mil) Molded SOJ	Military
	CY7C1049L-20VM	V36	36-Lead (400-Mil) Molded SOJ	
25	CY7C1049-25VC	V36	36-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1049L-25VC	V36	36-Lead (400-Mil) Molded SOJ	
	CY7C1049-25VI	V36	36-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1049L-25VI	V36	36-Lead (400-Mil) Molded SOJ	
	CY7C1049-25VM	V36	36-Lead (400-Mil) Molded SOJ	Military
	CY7C1049L-25VM	V36	36-Lead (400-Mil) Molded SOJ	

Shaded areas contain advance information.

Package Diagram

36-Lead (400-Mil) Molded SOJ V36





PRELIMINARY

CY7C1049

Document Title: CY7C1049 512K x 8 Static RAM
Document Number: 38-05063

REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	107256	09/10/01	SZV	Change from Spec number: 38-00563 to 38-05063

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